

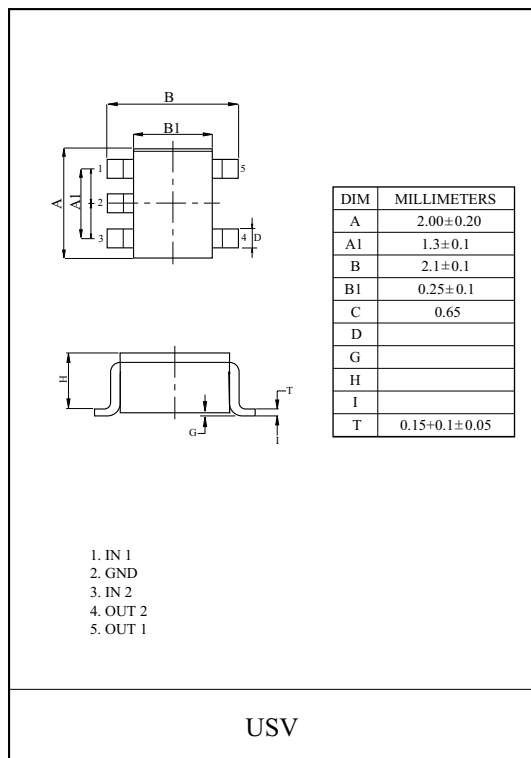
For EMI Filtering and ESD Protection.

FEATURES

- EMI/RFI filtering.
- ESD Protection to IEC 61000-4-2 Level 4.
- Filtering and ESD Protection for two data lines.
- Low insertion loss to 10MHz.
- Good attenuation of high frequency signals.
- Low clamping voltage.
- Low operating and leakage current.

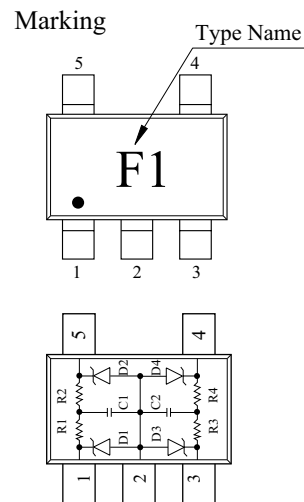
APPLICATIONS

- Cell phone handsets.
- Cell phone accessories.
- RF communications equipment.
- Laptop Computers.
- Two-way pagers.
- GPS Devices.



MAXIMUM RATING (Ta=25 °C)

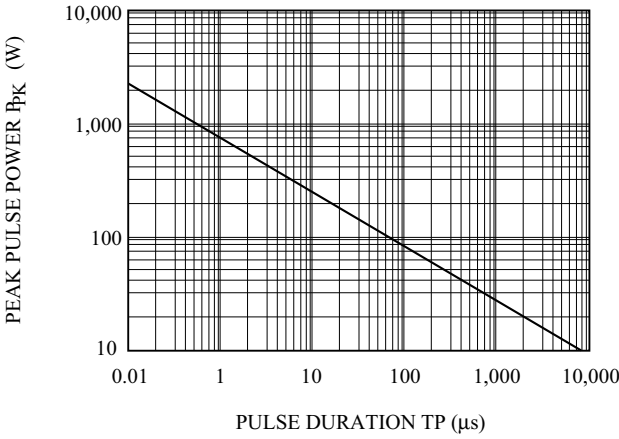
CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Pulse Power (tp=8/20/μs)	P _{PK}	175	W
Operating Temperature	T _j	-55 ~ 150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C



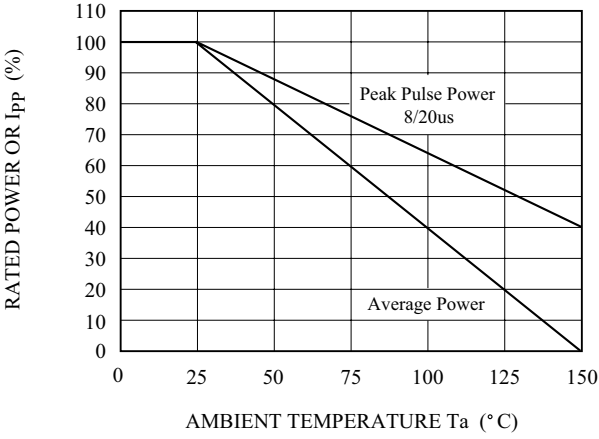
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V _{BR}	I _t =1mA	6	-	-	V
Reverse Leakage Current	I _R	V _{RWM} =3.3V	-	-	1	μA
		V _{RWM} =5V	-	-	5	
Junction Capacitance	C _J	V _R =0V, f=1MHz Between I/O Pins and GND each device	-	40	-	pF
Total Capacitance	C _T	V _R =0V, f=1MHz Between Input and Output, each Line	-	-	160	pF
Capacitor	C	Each Line	45	50	55	pF
Total Series Resistance	R	Each Line	-	100	-	Ω

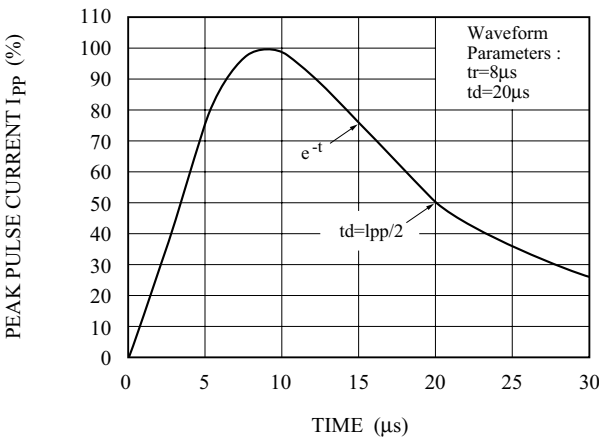
NON-REPETITIVE PEAK PULSE
POWER VS. PULSE TIME



POWER DERATION CURVE



PULSE WAVEFORM



S_{21} - f

